

DO NOT ENTER: /J.M./

AMENDMENTS TO THE CLAIMS

1-16. (Cancelled)

17. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0 mass % of P and 0.01-5.0 mass % of at least one metallic element selected from Cu and Bi, and P, Cu and Bi having a purity of at least 99.9 %.

18. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0 mass % of P, 0.01-2.0 mass % of at least one metallic element selected from In, Sn and Zn, 0.01 to 0.9 mass % of Au and/or 0.01-5.0 mass % of Pd and/or 0.01-0.9 mass % of Pt, and P, In, Sn, Zn, Au, Pd and Pt having a purity of at least 99.9 %.

19. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0 mass % of P, 0.01-2.0 mass % of at least one metallic element selected from In, Sn and Zn, and 0.05-5.0 mass % of at least one metallic element selected from Cu, Ni, Fe and Bi, and P, In, Sn, Zn, Cu, Ni, Fe and Bi having a purity of at least 99.9 %.

20. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0 mass % of P, 0.01-0.9 mass % of Au, and 0.01-5.0 mass % of at least one metallic element selected from Cu and Bi, and P, Au, Cu and Bi having a purity of at least 99.9 %.

21. (New) A sputtering target material for forming a thin film having high reflectance, said material being an Ag base alloy consisting of Ag having a purity of at least 99.95 %, 0.008-1.0

mass % of P, 0.01-2.0 mass % of at least one metallic element selected from In, Sn and Zn, 0.01-0.9 mass % of Au and/or 0.01-5.0 mass % of Pd and/or 0.01-0.9 mass % of Pt, and 0.01-5.0 mass % of at least one metallic element selected from Cu, Ni, Fe and Bi, and P, In, Sn, Zn, Au, Pd, Pt, Cu, Ni, Fe and Bi having a purity of at least 99.9 %.

22. (New) Thin film formed from the material of claim 17.

23. (New) Thin film formed from the material of claim 18.

24. (New) Thin film formed from the material of claim 19.

25. (New) Thin film formed from the material of claim 20.

26. (New) Thin film formed from the material of claim 21.